

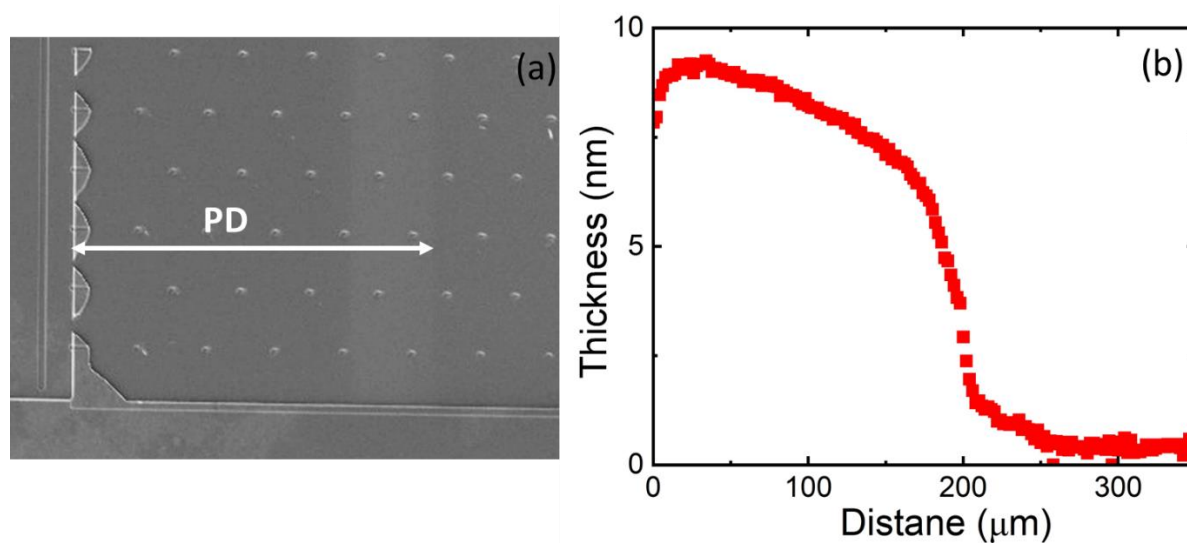
Low-temperature atomic-molecular layer deposition of air-stable and conformal Zn-benzenedithiol thin films

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**Figure 1.** (a) SEM images for a 10 nm Zn-BDT film grown in a LHAR chip and (b) the thickness profile for the same sample obtained using thin film analyzer reflectometer. The pulse and purge lengths for the deposition; 60 s  $[\text{Zn}(\text{DMP})_2]$  / 60 s  $\text{N}_2$  / 60 s BDT / 60 s  $\text{N}_2$ . The distance between the pillars (dots on the image) is 50 μm.